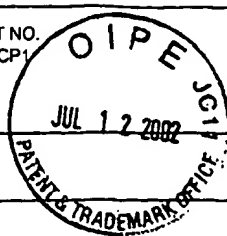


FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.196CP1	APPLICATION NO. 09/318,073
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Zhu, et al.	GROUP 2826
		FILING DATE May 25, 1999	



U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
WA		US 2001/0030886 A1	10/18/01	Thewes, et al.			
WA		US 2001/0050859 A1	12/13/01	Schwarzl			

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	

MSO-3132.DOC:afa  
070802

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APPLICANT  
Zhu, et al.FILING DATE  
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	5,861,328	1/19/99	Tehrani et al.			
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W	6,580,636 B2	06/17/03	Thewes et al.			

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
W	JP 2000 090658 A	3/31/00	Japan (Abstract)			X	

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W	Prinz, "Magnetoelectronics", Science Magazine, Vol. 282, Nov. 27, 1998.
	Wang et al., Feasibility of Ultra-Dense Spin-Tunneling Random Access Memory, IEEE Transactions on Magnetism, Vol. 33, No. 6, Nov. 1997.
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